

L Number	Hits	Search Text	DB	Time stamp
1	75	(porous near (silica (silicon adj (oxide dioxide)))) and ("low-k" "low k" (low adj (permittivity dielectric)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/21 14:44
2	99	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((porous near (silica (silicon adj (oxide dioxide)))) same ("low-k" "low k" (low adj (permittivity dielectric))))	USPAT; US-PGPUB	2004/08/21 14:58
-	8022	438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.	USPAT; US-PGPUB	2004/08/20 16:09
-	4776	(interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))	USPAT; US-PGPUB	2004/08/20 18:17
-	1106	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric))))	USPAT; US-PGPUB	2004/08/20 16:21
-	821	(liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6)	USPAT; US-PGPUB	2004/08/20 16:22
-	342	(porous near (silica (silicon adj (oxide dioxide)))) same ("low-k" "low k" (low adj (permittivity dielectric)))	USPAT; US-PGPUB	2004/08/20 16:28
-	151	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (hmds hexamethyldisilazane (silane adj coupler) (metal adj coupler))	USPAT; US-PGPUB	2004/08/20 16:34
-	11	(transistor fet mos mosfet (field adj effect)) same (gate source drain) same (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact) same (trace wir\$6 line interconnect\$6)	USPAT; US-PGPUB	2004/08/20 16:35
-	11	(transistor fet mos mosfet (field adj effect) gate source drain) and (liner etchstop (etch adj stop) nitride) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (via opening hole contact trace wir\$6 line interconnect\$6)	EPO; JPO; DERWENT; IBM_TDB	2004/08/20 16:41
-	139	(transistor fet mos mosfet (field adj effect) gate source drain) same (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6)	USPAT; US-PGPUB	2004/08/20 16:45
-	93	(liner etchstop (etch adj stop) nitride) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (via opening hole contact trace wir\$6 line interconnect\$6)	EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:22
-	291	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6))	USPAT; US-PGPUB	2004/08/20 18:15
-	441	borderless near contact	USPAT; US-PGPUB	2004/08/20 18:17
-	219	borderless near contact	EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:17

-	0	(borderless near contact) and (interlayer ild imd organic porous) and ("low-k" "low k" (low adj (permittivity dielectric)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:18
-	0	(borderless near contact) and ("low-k" "low k" (low adj (permittivity dielectric)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:18
-	36	((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and ((438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (hmds hexamethyldisilazane (silane adj coupler) (metal adj coupler)))	USPAT; US-PGPUB	2004/08/20 18:32
-	15	((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (borderless near contact)	USPAT; US-PGPUB	2004/08/20 18:38
-	8	(borderless near contact) same ("low-k" "low k" (low adj (permittivity dielectric)))	USPAT; US-PGPUB	2004/08/20 18:46
-	50	(borderless near contact) and (interlayer ild imd organic porous)	EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:51
-	72	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (borderless near contact)	USPAT; US-PGPUB	2004/08/20 18:56